

MRF10070H*

Microwave Pulse Power Transistor
70 Watts Peak NPN 1025–1150 MHz



AVAILABLE AS

1) JANTX: MRF10070HX
 2) JANTXV: MRF10070HXV
 3) JANS: MRF10070HS
 4) COML+: MRF10070HC

PACKAGE: Case 376C-01

- Designed for 1025–1150 MHz pulse common base amplifiers.
- Guaranteed Performance at 1090 MHz
 - Output Power = 70 Watts Peak
 - Gain = 9.0 dB Min
 - 100% Tested for Load Mismatch at All Phase Angles with 10:1 VSWR
 - Characterized with 10 μ s, 10% Duty Cycle Pulses
 - Silicon Nitride Passivated
 - Gold Metallized, Emitter Ballasted for Long Life
 - Internal Input and Output Matching
 - Hermetically Sealed Package

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CES}	65	Vdc
Collector-Base Voltage	V_{CBO}	65	Vdc
Emitter-Base Voltage	V_{EBO}	3.5	Vdc
Collector Current – Peak (1)	I_C	8.8	Adc
Device Dissipation at $T_C = 25^\circ\text{C}$ (1 & 2) Derate above 25 $^\circ\text{C}$	P_D	438 2.5	W W/ $^\circ\text{C}$
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case (3)	$R_{\theta JC}$	0.4	$^\circ\text{C}/\text{W}$

NOTES:

1. Under pulse RF operating conditions.
2. These devices are designed for RF operation. The total device dissipation rating applies only when the devices are operated as RF amplifiers.
3. Thermal Resistance is determined under specified RF operating conditions by infrared measurement techniques.

(continued)

*Motorola Preferred Device. **Preferred** devices are Motorola recommended choices for future use and best overall value.

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ELECTRICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage ($I_C = 60\text{ mAdc}$, $V_{BE} = 0$)	$V_{(BR)CES}$	65	–	Vdc
Collector-Base Breakdown Voltage ($I_C = 60\text{ mAdc}$, $I_E = 0$)	$V_{(BR)CBO}$	65	–	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\text{ mAdc}$, $I_C = 0$)	$V_{(BR)EBO}$	3.5	–	Vdc
Collector Cutoff Current ($V_{CB} = 36\text{ Vdc}$, $I_E = 0$)	I_{CBO}	–	25	mAdc

ON CHARACTERISTICS

DC Current Gain ($I_C = 5.0\text{ Adc}$, $V_{CE} = 5.0\text{ Vdc}$)	h_{FE}	20	–	–
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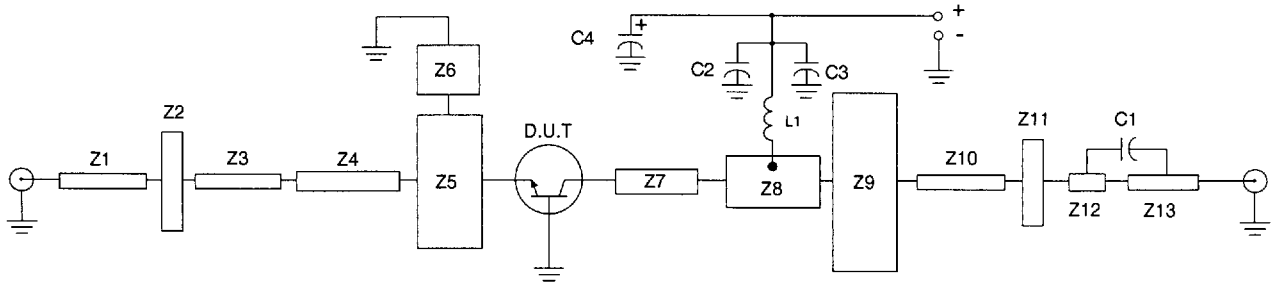
FUNCTIONAL TESTS

Common-Base Amplifier Power Gain ($V_{CC} = 50\text{ Vdc}$, $P_{OUT} = 70\text{ W Peak}$, $f = 1090\text{ MHz}$)	G_{PB}	9.0	–	dB
Collector Efficiency ($V_{CC} = 50\text{ Vdc}$, $P_{OUT} = 70\text{ W Peak}$, $f = 1090\text{ MHz}$)	η	40	–	%
Load Mismatch ($V_{CC} = 50\text{ Vdc}$, $P_{OUT} = 70\text{ W Peak}$, $f = 1090\text{ MHz}$, Load VSWR = 10:1 All Phase Angles)	ψ	No Degradation in Output Power		

ASSURANCE TESTING (Pre/Post Burn-In)

Burn-In Test Conditions: $V_{CB} \geq 10\text{ Vdc}$, $T_J = 162.5\text{ }^\circ\text{C} + 12.5\text{ }^\circ\text{C}$

Characteristic	Symbol	Min	Max	Unit
Collector Cutoff Current ($V_{CB} = 50\text{ Vdc}$, $I_E = 0$)	I_{CBO}	–	25	mAdc
DC Current Gain ($I_C = 5.0\text{ Adc}$, $V_{CE} = 5.0\text{ Vdc}$)	h_{FE}	20	–	–



C1 – 82pF 100 mil Chip Capacitor
 C2 – 82 pF 100 mil Chip Capacitor
 C3 – 0.1 μ F
 C4 – 100 μ F/100 Vdc Electrolytic

L1 – 3 turns #18 AWG, 1/8" ID, 0.18" Long
 Z1-Z13 – Microstrip, see details below
 Board Material – 0.030" Glass Teflon®
 2 Oz. Copper, $\epsilon_r = 2.55$

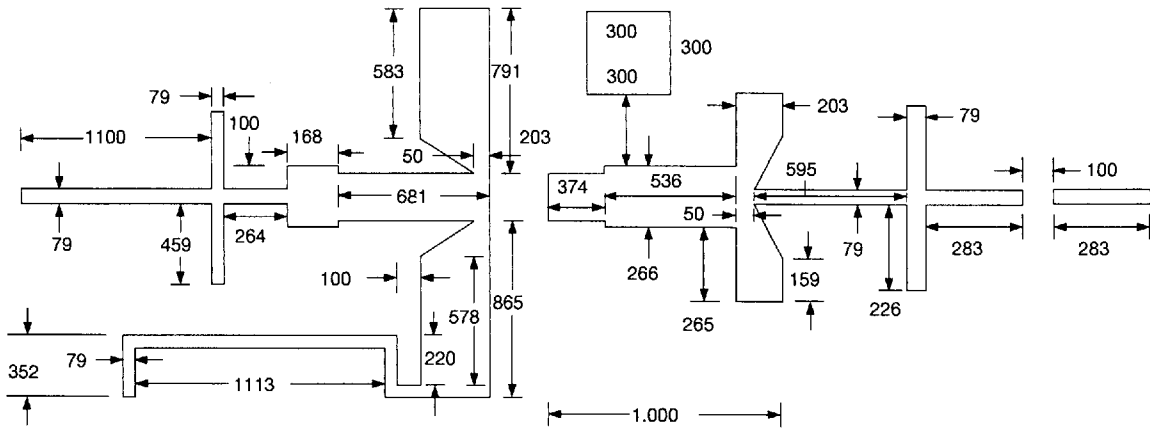


Figure 1. Test Circuit

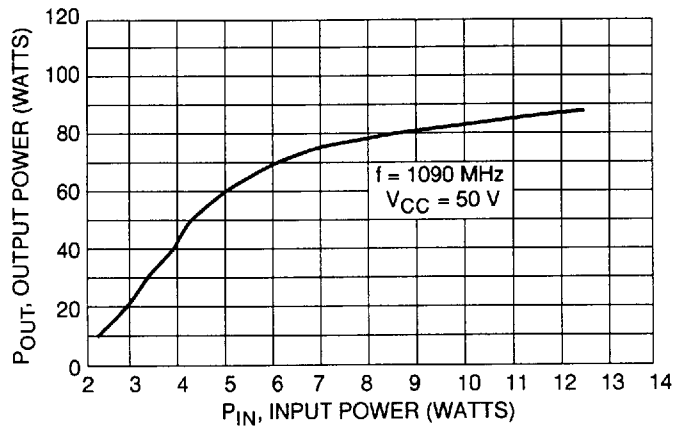
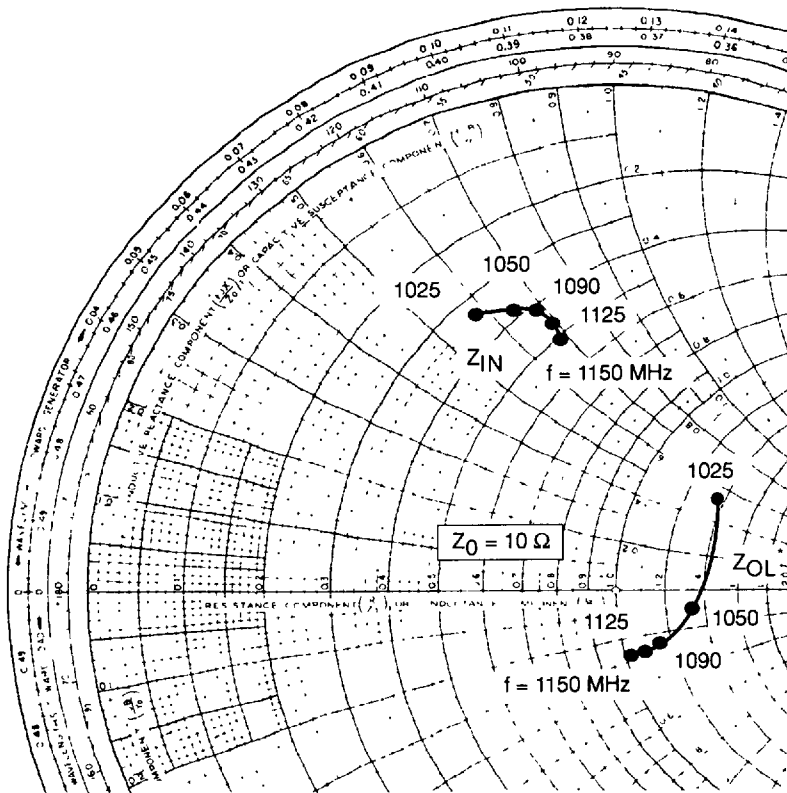


Figure 2. Output Power versus Input Power



$P_{OUT} = 70 \text{ W Pk}, V_{CC} = 50 \text{ V}$

f MHz	Z_{IN} OHMS	Z_{OL}^* (Z_{OUT}) OHMS
1025	$3.3 + j5.8$	$14.3 + j5.6$
1050	$3.6 + j6.5$	$13.3 - j1.0$
1090	$4.0 + j6.9$	$11.3 - j2.1$
1125	$4.5 + j6.9$	$10.4 - j2.5$
1150	$5.0 + j6.9$	$10.2 - j2.6$

Z_{OL}^* is the conjugate of the optimum load impedance into which the device operates at a given output power, voltage and frequency.

Figure 3. Series Equivalent Input/Output Impedances

TABLE 1. SCREENING REQUIREMENTS

SCREEN	METHOD	HX	HXV
1. Internal visual inspection (precap)	2072	N/A	100%
2. High temperature non-operating life	1032	100%	100%
3. Temperature cycling	1051	100%	100%
4. Constant Acceleration (Gold wires only)	2006	100%	100%
5. Hermetic seal (Fine and Gross)	1071	100%	100%
6. Establish Unit Identity	none	100%	100%
7. Interim electrical parameters	as specified	100%	100%
8. High temperature reverse bias (HTRB)	1039	100%	100%
9. Interim electrical parameters	as specified	100%	100%
10. Power burn-in	1039	100%	100%
11. Final electrical parameters	as specified	100%	100%
12. Hermetic seal (Fine and Gross)	1071	optional	optional

GROUP A TEST SEQUENCE

Subgroups			
A1	A2	A3	A4
Type of Test			
Visual/Mechanical Package: Dimensions, Marking	DC Tests V(BR)CBO V(BR)CES V(BR)EBO I _{CBO} h _{FE}	Hi/Lo Temp Not Applicable	AC Tests G _{PB} η

GROUP B TEST SEQUENCE

Subgroups					
B1**	B2*	B3*	B4	B5	B6*
Type of Test					
Solderability (1) Resistance to Solvents	Temp. Cycling Hermetic Seal Fine Gross	Steady State Operating Life Bond Strength	Decap Visual	Not Required	High Temp. Life (Non-Operating)

* The tests in this subgroup are preceded and followed by I_{CBO} and h_{FE} electrical tests.

** Separate samples may be used for each test.

(1) Omit Steam Aging requirements.

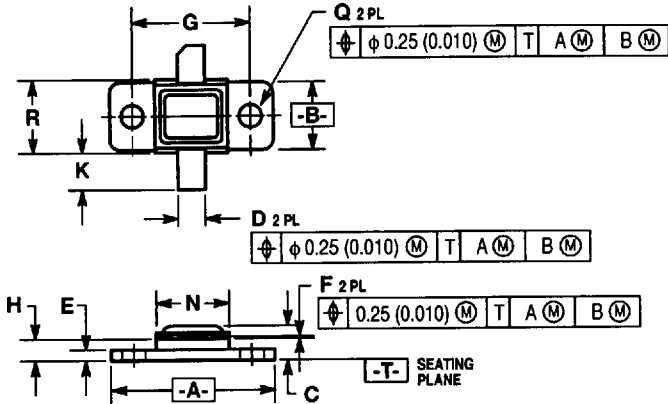
GROUP C TEST SEQUENCE*

Subgroups					
C1	C2**	C3**	C4	C5	C6**
Type of Test					
Physical Dimensions	Thermal Shock (Glass Strain) Terminal Strength Hermetic Seal Moist. Resistance	Mech. Shock Vibration (Var. Freq.) Const. Accel.	Salt Atmosphere	Not Applicable	Steady State Op Life

* Group C is performed on the initial lot and requalification only..

** The tests in this subgroup are preceded and followed by I_{CBO} and h_{FE} electrical tests.

OUTLINE DIMENSIONS



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	22.61	23.11	0.890	0.910
B	9.40	10.16	0.370	0.400
C	4.83	5.33	0.190	0.210
D	3.56	4.06	0.140	0.160
E	1.40	1.65	0.055	0.065
F	0.08	0.15	0.003	0.006
G	16.51 BSC		0.650 BSC	
H	2.80	3.30	0.110	0.130
K	4.57	5.59	0.180	0.220
N	9.91	10.41	0.390	0.410
Q	2.93	3.42	0.115	0.135
R	9.91	10.41	0.390	0.410

CASE 376C-01

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